HD74HCT620/HD74HCT623

Octal Bus Transceivers (with inverted 3-state outputs)/
Octal Bus Transceivers (with 3-state outputs)

HITACHI

Description

This octal transceiver is designed for asynchronous two-way communication between data buses. The control function implementation allows for maximum flexibility in timng.

This device allows data transmission from A bus to the B bus or from the B bus to the A bus depending upon the logic levels at the enable inputs ($\overline{GBA}$ and GAB).

The enable inputs can be used to disable the device so that the buses are affectively isolated.

The dual-enable configuration gives these devices the capability to store data by simultaneous enabling of $\overline{GBA}$ and GAB. Each output reinforces its input in this transceiver configuration. Thus, when both control inputs are enabled and all other data sources to the two sets of bus lines are at high impedance, both sets of bus lines (16 in all) will remain at their last states. The 8-bit codes appearing on the two sets of buses will be identical for the HD74HCT623 or complementary for the HD74HCT620.

Features

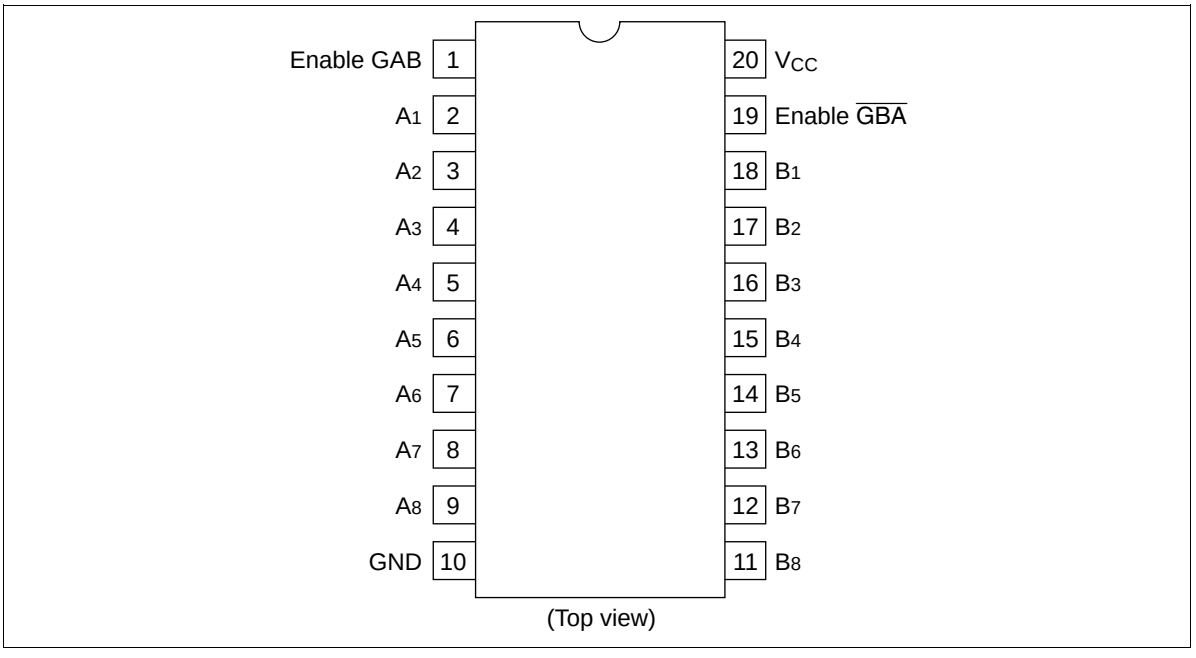
- LSTTL Output Logic Level Compatibility as well as CMOS Output Compatibility
- High Speed Operation: t_{pd} (Bus to Bus) = 15 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: V_{CC} = 4.5 to 5.5 V
- Low Input Current: 1 µA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 µA max (Ta = 25°C)

Hitachi semiconductor

Function Table

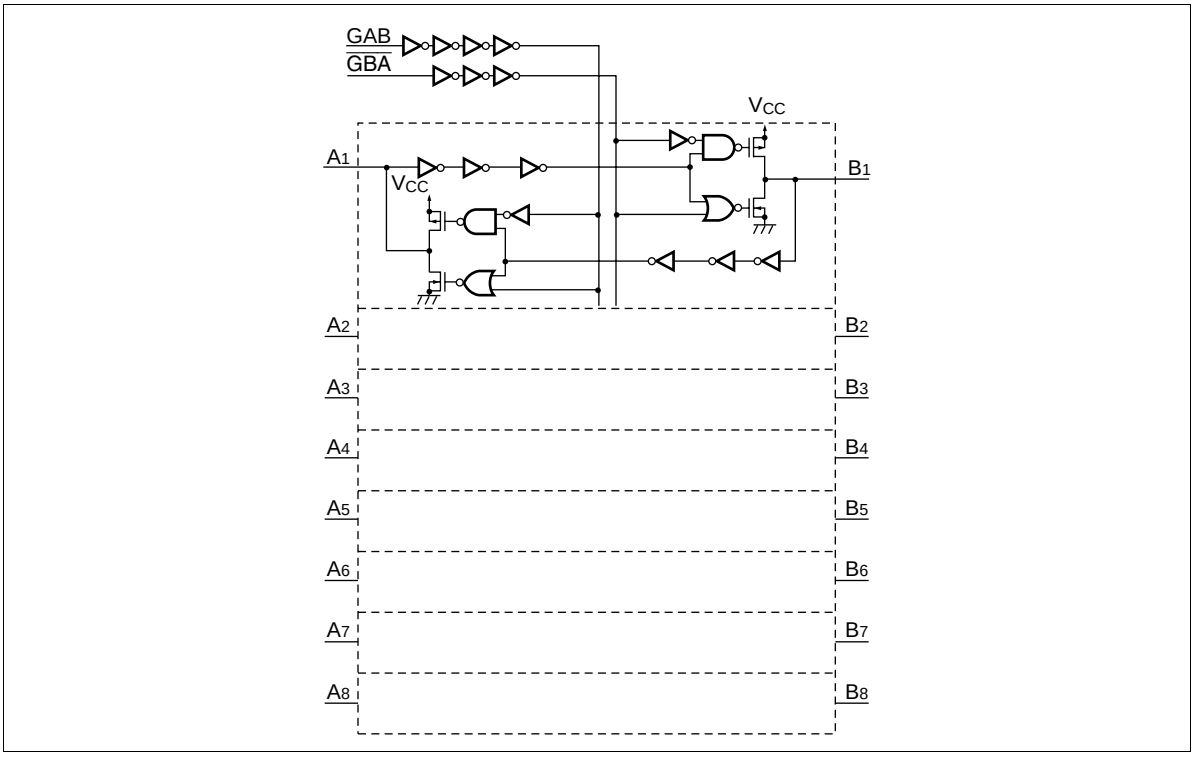
Enable Input		Operation	
$\overline{GBA}$	GAB	HD74HCT620	HD74HCT623
L	L	$\overline{B}$ data to A bus	B data to A bus
H	H	$\overline{A}$ data to B bus	A data to B bus
H	L	Isolation	Isolation
L	H	$\overline{B}$ data to A bus, $\overline{A}$ data to B bus	B data to A bus, A data to B bus

Pin Arrangement

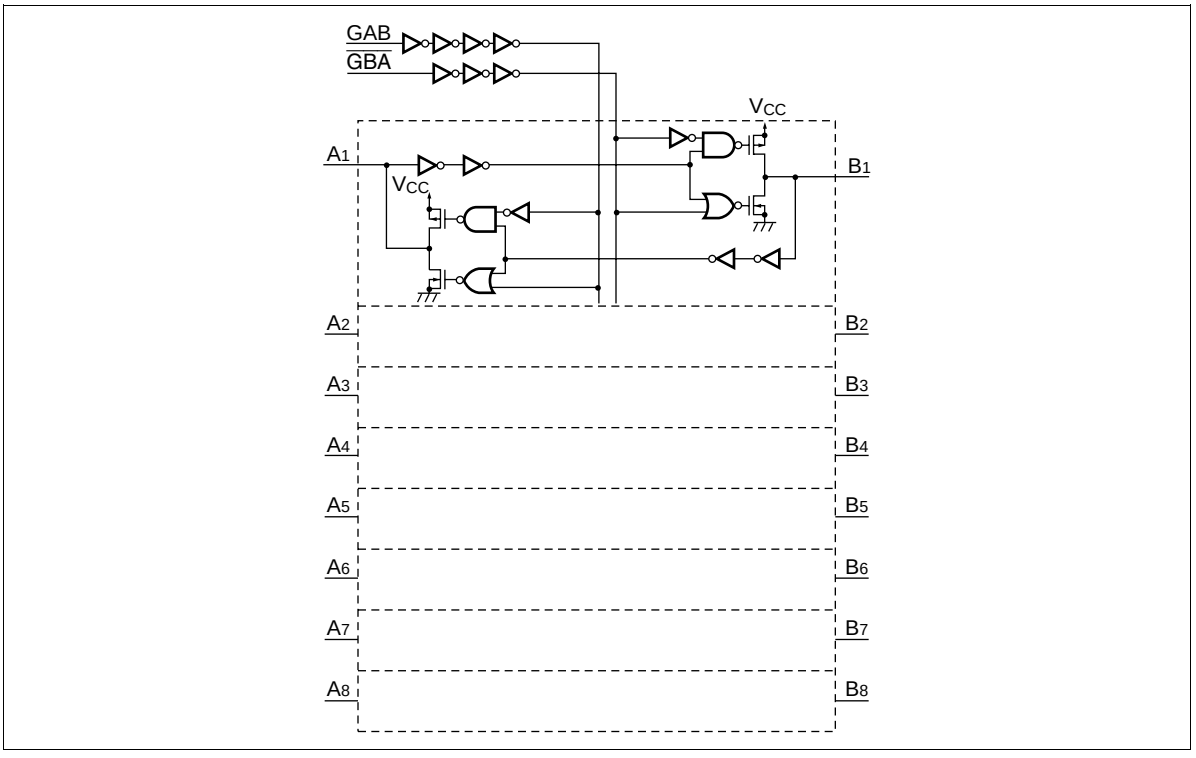


Block Diagram

HD74HCT620



HD74HCT623



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} + 0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} + 0.5	V
DC current drain per pin	I_{OUT}	±35	mA
DC current drain per V_{CC}, GND	I_{CC}, I_{GND}	±75	mA
DC input diode current	I_{IK}	±20	mA
DC output diode current	I_{OK}	±20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	–65 to +150	°C

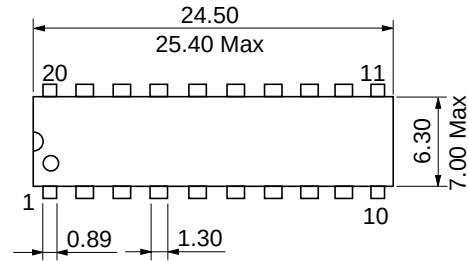
DC Characteristics

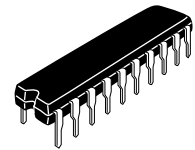
Item	Symbol	Ta = 25°C Min	Typ	Max	Ta = –40 to +85°C Min	Max	Unit	Test Conditions V_{CC} (V)	
Input voltage	V_{IH}	2.0	—	—	2.0	—	V	4.5 to 5.5	
	V_{IL}	—	—	0.8	—	0.8	V	4.5 to 5.5	
Output voltage	V_{OH}	4.4	—	—	4.4	—	V	4.5	Vin = V_{IH} or V_{IL} I_{OH} = –20 µA
		4.18	—	—	4.13	—		4.5	I_{OH} = –6 mA
	V_{OL}	—	—	0.1	—	0.1	V	4.5	Vin = V_{IH} or V_{IL} I_{OL} = 20 µA
		—	—	0.26	—	0.33		4.5	I_{OL} = 6 mA
Off-state output current	I_{OZ}	—	—	±0.5	—	±5.0	µA	5.5	Vin = V_{IH} or V_{IL}, Vout = V_{CC} or GND
Input current	Iin	—	—	±0.1	—	±1.0	µA	5.5	Vin = V_{CC} or GND
Quiescent supply current	I_{CC}	—	—	4.0	—	40	µA	5.5	Vin = V_{CC} or GND, Iout = 0 µA

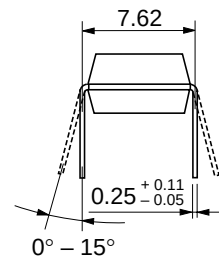
AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

Item	Symbol	Ta = 25°C Min	Typ	Max	Ta = –40 to +85°C Min	Max	Unit	Test Conditions V_{CC} (V)
Propagation delay	t_{PLH}	—	13	20	—	25	ns	4.5
time	t_{PHL}	—	16	20	—	25		4.5
Output enable	t_{ZH}	—	16	30	—	38	ns	4.5
time	t_{ZL}	—	16	30	—	38		4.5
Output disable	t_{HZ}	—	19	30	—	38	ns	4.5
time	t_{LZ}	—	21	30	—	38		4.5
Output rise/fall time	t_{TLH} t_{THL}	—	4	12	—	15	ns	4.5
Input capacitance	Cin	—	5	10	—	10	pF	—

Unit: mm

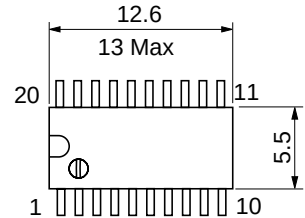


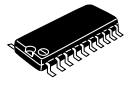


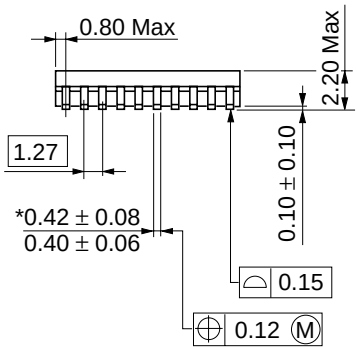


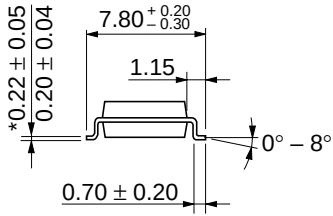
Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.26 g

Unit: mm





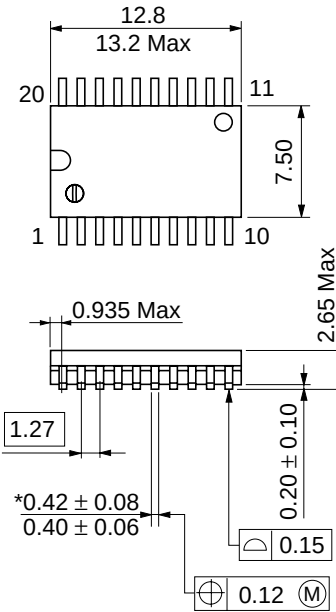


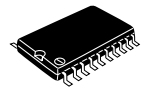


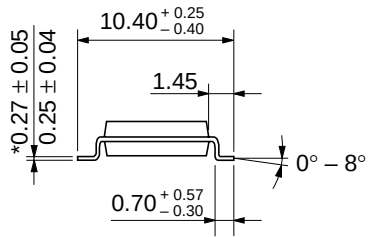
*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.31 g

Unit: mm







*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
NorthAmerica : http:semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
Asia (Singapore) : http://www.has.hitachi.com.sg/grp3/sicd/index.htm
Asia (Taiwan) : http://www.hitachi.com.tw/E/Product/SICD_Frame.htm
Asia (HongKong) : http://www.hitachi.com.hk/eng/bo/grp3/index.htm
Japan : http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX